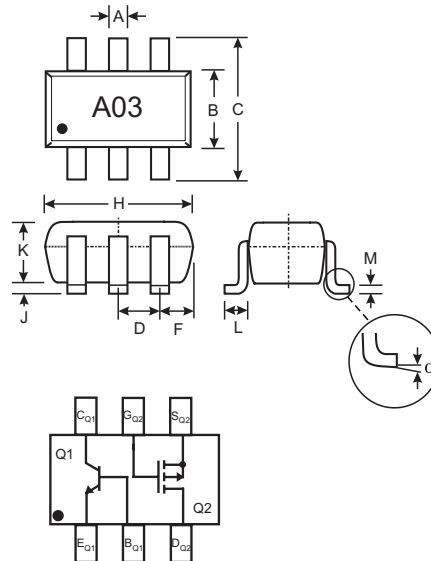


Features

- Combines MMBT4401 type transistor with BSS84 type MOSFET
- Small Surface Mount Package
- PNP/N-Channel Complement Available: CTA2P1N
- **Lead Free/RoHS Compliant (Note 2)**

Mechanical Data

- Case: SOT-363
- Case Material: Molded Plastic. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020C
- Terminals: Solderable per MIL-STD-202, Method 208
- Lead Free Plating (Matte Tin Finish annealed over Alloy 42 leadframe).
- Terminal Connections: See Diagram
- Marking: A03, See Page 3
- Ordering Information: See Page 3
- Weight: 0.006 grams (approx.)



SOT-363		
Dim	Min	Max
A	0.10	0.30
B	1.15	1.35
C	2.00	2.20
D	0.65 Nominal	
F	0.30	0.40
H	1.80	2.20
J	—	0.10
K	0.90	1.00
L	0.25	0.40
M	0.10	0.25
α	0°	8°
All Dimensions in mm		

Maximum Ratings, Total Device @ $T_A = 25^\circ\text{C}$ unless otherwise specified

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 1)	P_d	150	mW
Thermal Resistance, Junction to Ambient (Note 1)	$R_{\theta JA}$	833	$^\circ\text{C/W}$
Operating and Storage and Temperature Range	T_j, T_{STG}	-55 to +150	$^\circ\text{C}$

Maximum Ratings, Q1, MMBT4401 NPN Transistor Element @ $T_A = 25^\circ\text{C}$ unless otherwise specified

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V_{CBO}	60	V
Collector-Emitter Voltage	V_{CEO}	40	V
Emitter-Base Voltage	V_{EBO}	6.0	V
Collector Current - Continuous	I_C	600	mA

Maximum Ratings, Q2, BSS84 P-Channel MOSFET Element @ $T_A = 25^\circ\text{C}$ unless otherwise specified

Characteristic	Symbol	Value	Units
Drain-Source Voltage	V_{DSS}	-50	V
Drain-Gate Voltage $R_{GS} \leq 1.0\text{M}\Omega$	V_{DGR}	-50	V
Gate-Source Voltage Continuous	V_{GSS}	± 20	V
Drain Current Continuous	I_D	-130	mA

- Notes: 1. Device mounted on FR-4 PCB, 1 inch x 0.85 inch x 0.062 inch; pad layout as shown on Diodes Inc. suggested pad layout document AP02001, which can be found on our website at <http://www.diodes.com/datasheets/ap02001.pdf>.
2. No purposefully added lead.

Electrical Characteristics, Q1, MMBT4401 NPN Transistor Element

 @ $T_A = 25^\circ\text{C}$ unless otherwise specified

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Characteristic	Symbol	Min	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 3)					
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	60	—	V	$I_C = 100\mu\text{A}$, $I_E = 0$
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	40	—	V	$I_C = 1.0\text{mA}$, $I_B = 0$
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	6.0	—	V	$I_E = 100\mu\text{A}$, $I_C = 0$
Collector Cutoff Current	I_{CEX}	—	100	nA	$V_{CE} = 35\text{V}$, $V_{EB(OFF)} = 0.4\text{V}$
Base Cutoff Current	I_{BL}	—	100	nA	$V_{CE} = 35\text{V}$, $V_{EB(OFF)} = 0.4\text{V}$
ON CHARACTERISTICS (Note 3)					
DC Current Gain	h_{FE}	20 40 80 100 40	— — — 300 —	—	$I_C = 100\mu\text{A}$, $V_{CE} = 1.0\text{V}$ $I_C = 1.0\text{mA}$, $V_{CE} = 1.0\text{V}$ $I_C = 10\text{mA}$, $V_{CE} = 1.0\text{V}$ $I_C = 150\text{mA}$, $V_{CE} = 1.0\text{V}$ $I_C = 500\text{mA}$, $V_{CE} = 2.0\text{V}$
Collector-Emitter Saturation Voltage	$V_{CE(SAT)}$	—	0.40 0.75	V	$I_C = 150\text{mA}$, $I_B = 15\text{mA}$ $I_C = 500\text{mA}$, $I_B = 50\text{mA}$
Base-Emitter Saturation Voltage	$V_{BE(SAT)}$	0.75 —	0.95 1.2	V	$I_C = 150\text{mA}$, $I_B = 15\text{mA}$ $I_C = 500\text{mA}$, $I_B = 50\text{mA}$
SMALL SIGNAL CHARACTERISTICS					
Output Capacitance	C_{cb}	—	6.5	pF	$V_{CB} = 5.0\text{V}$, $f = 1.0\text{MHz}$, $I_E = 0$
Input Capacitance	C_{eb}	—	30	pF	$V_{EB} = 0.5\text{V}$, $f = 1.0\text{MHz}$, $I_C = 0$
Input Impedance	h_{ie}	1.0	15	k Ω	$V_{CE} = 10\text{V}$, $I_C = 1.0\text{mA}$, $f = 1.0\text{kHz}$
Voltage Feedback Ratio	h_{re}	0.1	8.0	$\times 10^{-4}$	
Small Signal Current Gain	h_{fe}	40	500	—	
Output Admittance	h_{oe}	1.0	30	μS	
Current Gain-Bandwidth Product	f_T	250	—	MHz	$V_{CE} = 10\text{V}$, $I_C = 20\text{mA}$, $f = 100\text{MHz}$
SWITCHING CHARACTERISTICS					
Delay Time	t_d	—	15	ns	$V_{CC} = 30\text{V}$, $I_C = 150\text{mA}$, $V_{BE(off)} = 2.0\text{V}$, $I_{B1} = 15\text{mA}$
Rise Time	t_r	—	20	ns	
Storage Time	t_s	—	225	ns	$V_{CC} = 30\text{V}$, $I_C = 150\text{mA}$, $I_{B1} = I_{B2} = 15\text{mA}$
Fall Time	t_f	—	30	ns	

Electrical Characteristics, Q2, BSS84 P-Channel MOSFET Element

 @ $T_A = 25^\circ\text{C}$ unless otherwise specified

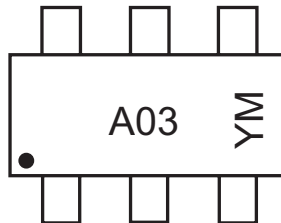
Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 3)						
Drain-Source Breakdown Voltage	BV _{DSS}	-50	—	—	V	V _{GS} = 0V, I _D = -250μA
Zero Gate Voltage Drain Current	I _{DSS}	—	—	-15 -60 -100	μA μA nA	V _{DS} = -50V, V _{GS} = 0V, T _J = 25°C V _{DS} = -50V, V _{GS} = 0V, T _J = 125°C V _{DS} = -25V, V _{GS} = 0V, T _J = 25°C
Gate-Body Leakage	I _{GSS}	—	—	±10	nA	V _{GS} = ±20V, V _{DS} = 0V
ON CHARACTERISTICS (Note 3)						
Gate Threshold Voltage	V _{GS(th)}	-0.8	—	-2.0	V	V _{DS} = V _{GS} , I _D = -1mA
Static Drain-Source On-Resistance	R _{DS(ON)}	—	—	10	Ω	V _{GS} = -5V, I _D = 0.100A
Forward Transconductance	g _{FS}	.05	—	—	S	V _{DS} = -25V, I _D = 0.1A
DYNAMIC CHARACTERISTICS						
Input Capacitance	C _{iss}	—	—	45	pF	V _{DS} = -25V, V _{GS} = 0V f = 1.0MHz
Output Capacitance	C _{oss}	—	—	25	pF	
Reverse Transfer Capacitance	C _{rss}	—	—	12	pF	
SWITCHING CHARACTERISTICS						
Turn-On Delay Time	t _{D(ON)}	—	10	—	ns	V _{DD} = -30V, I _D = -0.27A, R _{GEN} = 50Ω, V _{GS} = -10V
Turn-Off Delay Time	t _{D(OFF)}	—	18	—	ns	

Notes: 3. Short duration pulse test used to minimize self-heating effect.

Ordering Information (Note 4)

Device	Packaging	Shipping
CTA2N1P-7-F	SOT-363	3000/Tape & Reel

Notes: 4. For Packaging Details, go to our website at <http://www.diodes.com/datasheets/ap02007.pdf>.

Marking Information


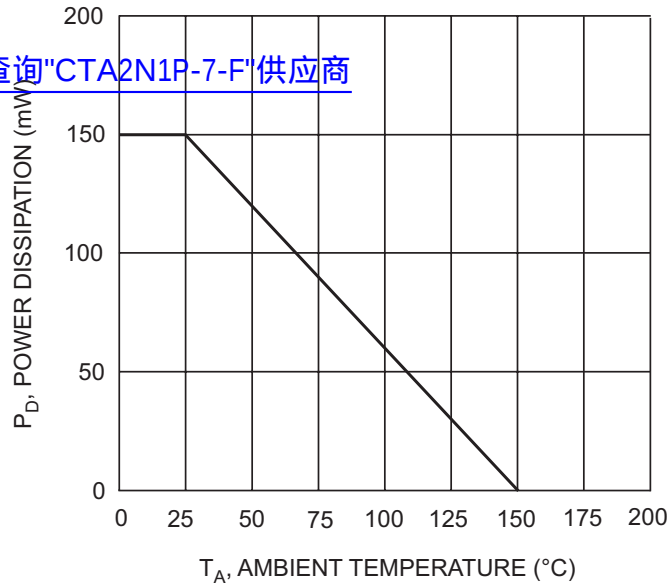
A03 = Product Type Marking Code
 YM = Date Code Marking
 Y = Year ex: N = 2002
 M = Month ex: 9 = September

Date Code Key

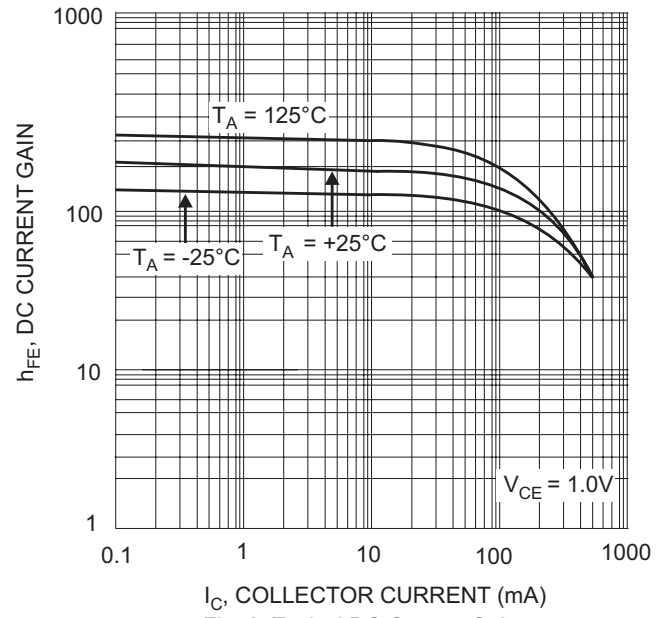
Year	2001	2002	2003	2004	2005	2006	2007	2008	2009
Code	M	N	P	R	S	T	U	V	W

Month	Jan	Feb	March	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

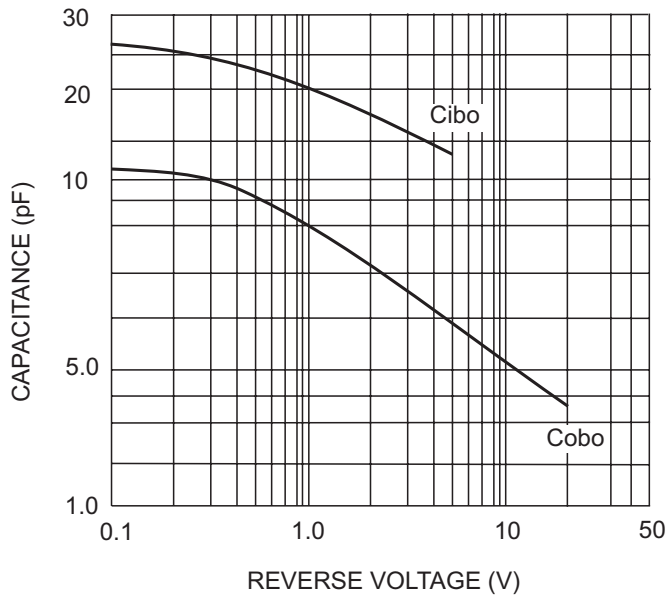
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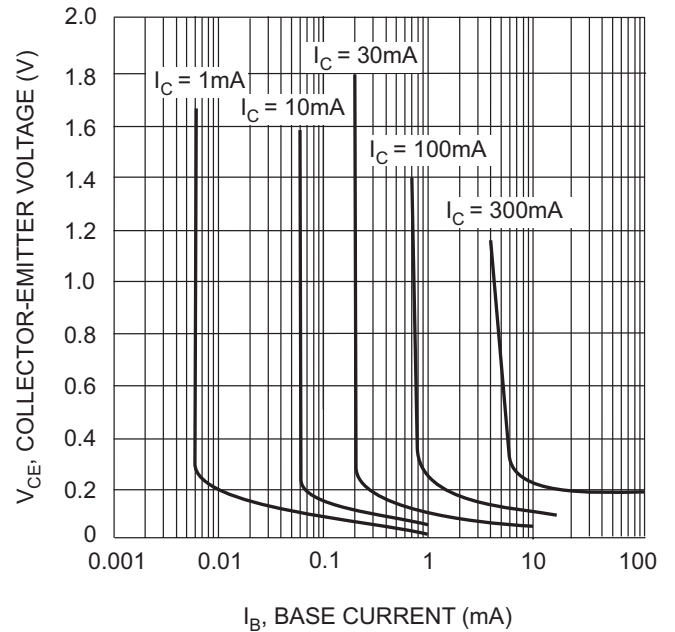
T_A , AMBIENT TEMPERATURE (°C)
Fig. 1 Max Power Dissipation vs Ambient Temperature (Total Device)



I_C , COLLECTOR CURRENT (mA)
Fig. 2 Typical DC Current Gain vs Collector Current



REVERSE VOLTAGE (V)
Fig. 3 Typical Capacitance



I_B , BASE CURRENT (mA)
Fig. 4 Typical Collector Saturation Region

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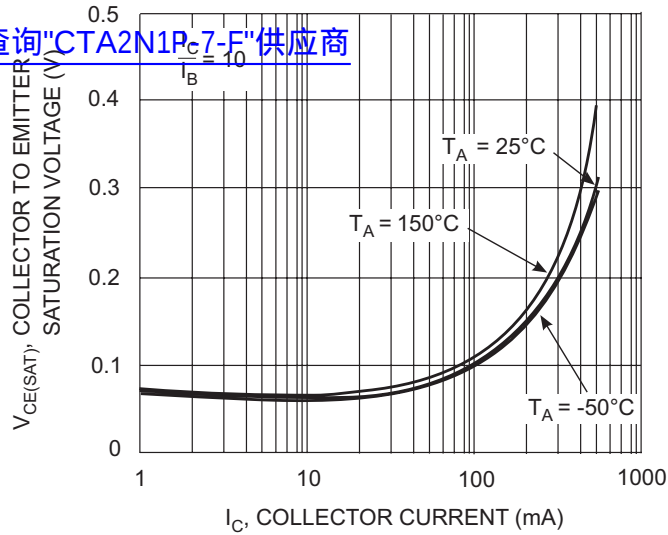


Fig. 5 Collector Emitter Saturation Voltage vs. Collector Current

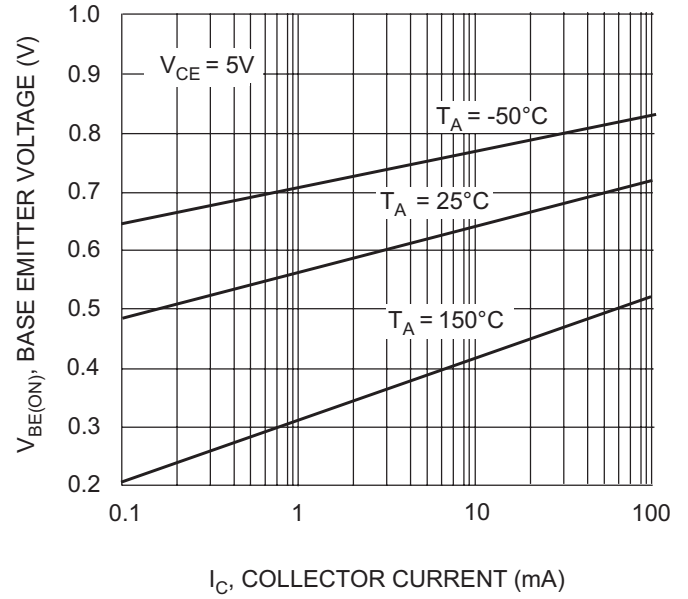


Fig. 6 Base Emitter Voltage vs. Collector Current

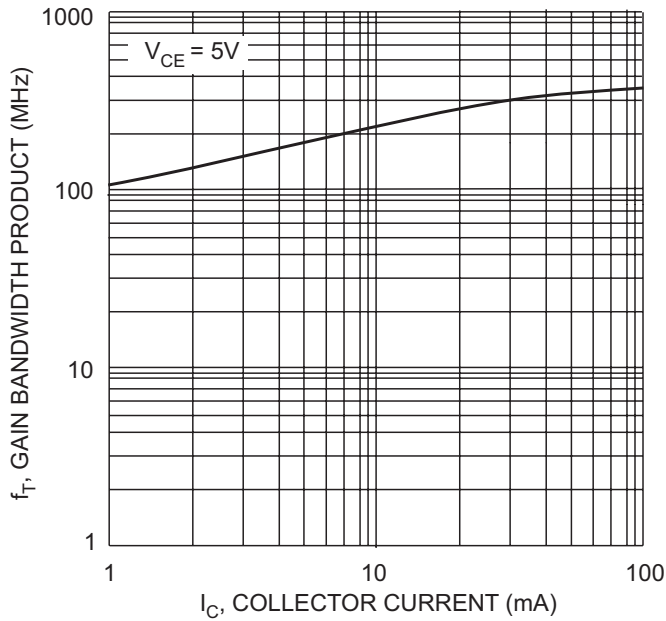
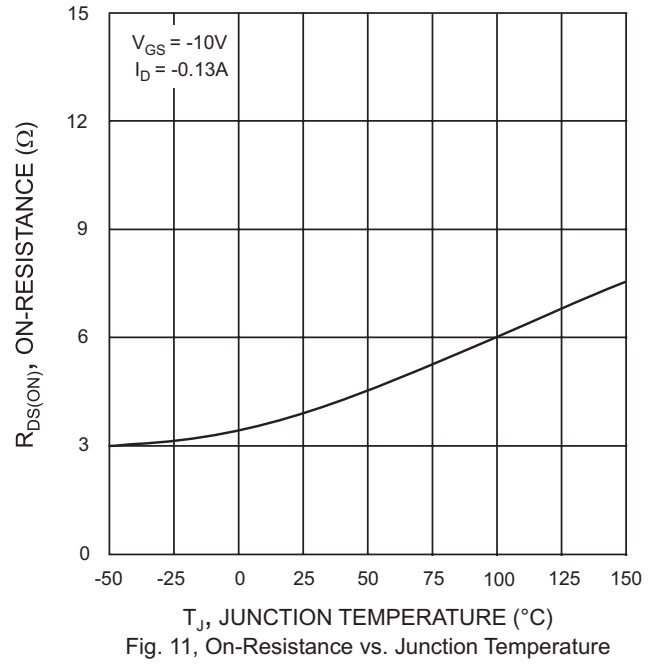
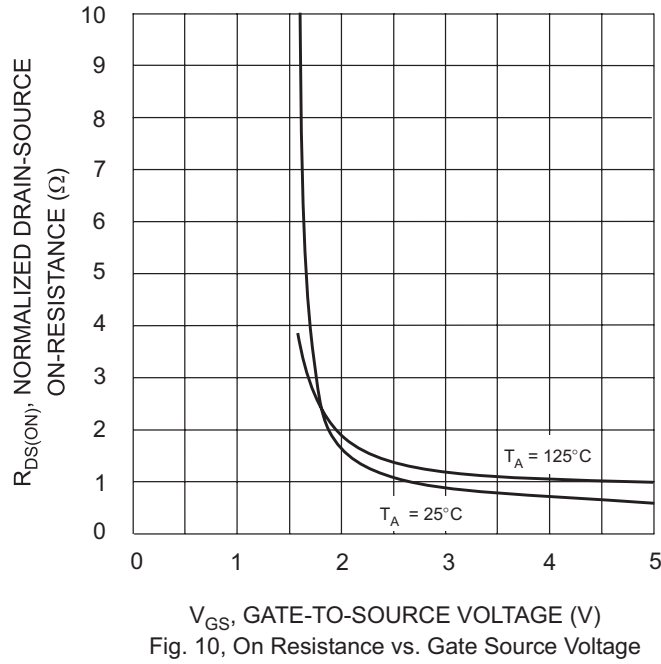
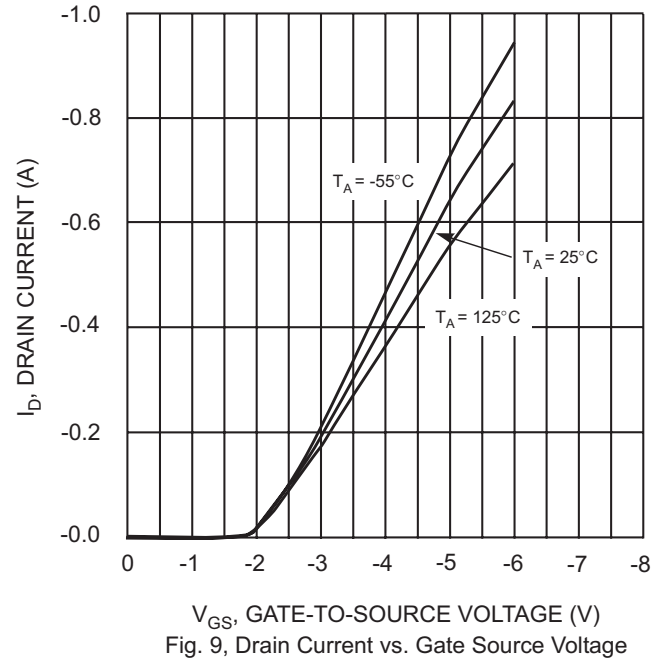
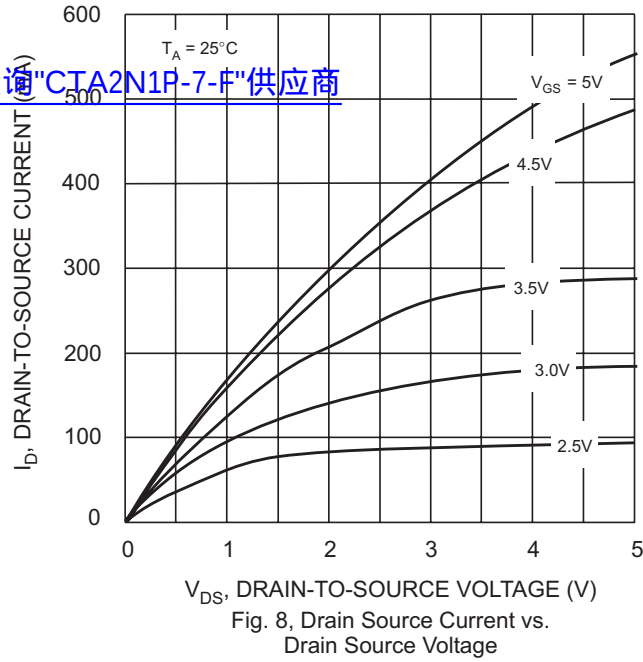


Fig. 7 Gain Bandwidth Product vs. Collector Current

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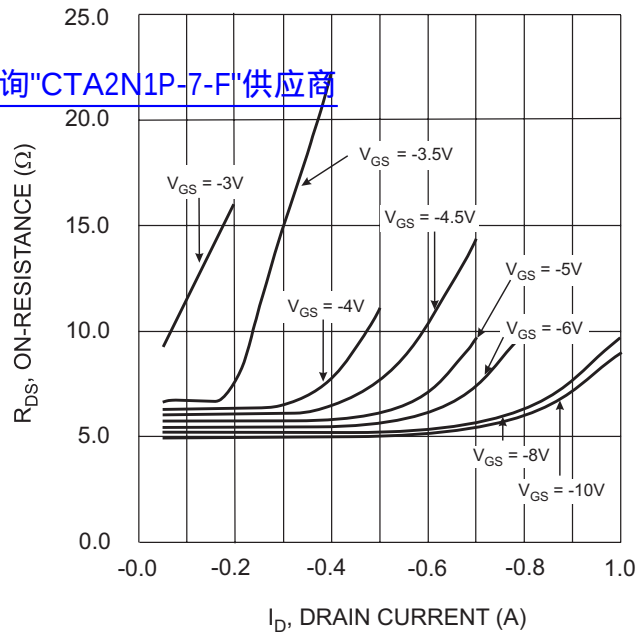
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Fig. 12, On-Resistance vs. Drain Current

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